

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

\$9018 TRANSISTOR (NPN)

FEATURES

Power dissipation

 P_{CM} : 0.4 W(Tamb=25)

Collector current

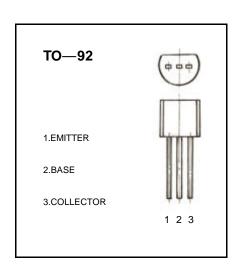
I_{CM} : 0.05 A

Collector-base voltage

 $V_{(BR)CBO}$: 25 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150



ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

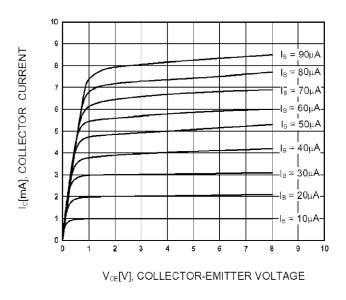
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	Ic= 100 μ A , I _E =0	25			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	Ic= 0.1 mA , I _B =0	18			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100 μ A , I _C =0	4			V
Collector cut-off current	Ісво	V _{CB} = 20 V			0.1	μА
Collector cut-off current	I _{CEO}	V _{CE} = 15 V			0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 3 V , I _C =0			0.1	μА
DC current gain	h _{FE(1)}	V _{CE} = 5 V, I _C = 1mA	28		270	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =10 mA, I _B =1mA			0.5	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =10mA , I _B =1mA			1.4	V
Transition frequency	f⊤	V _{CE} =5 V, b=5 mA f =400MHz	600			MHz

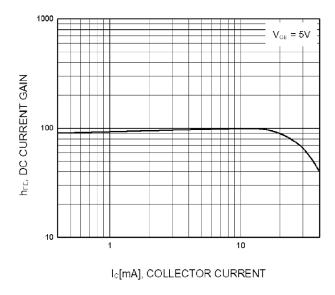
CLASSIFICATION OF h_{FE(1)}

Rank	D	E	F	G	Н	I	J
Range	28-45	39-60	54-80	72-108	97-146	132-198	180-270

Typical Characteristics

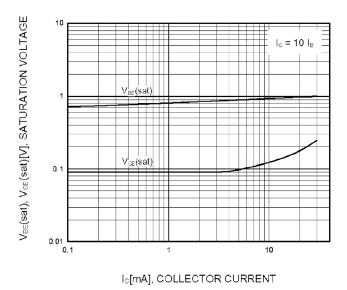
S9018

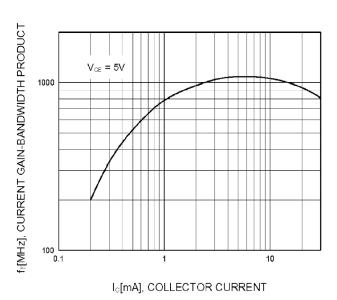




Static Characteristic

DC Current Gain





Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

Current Gain Bandwidth Product

TO-92 PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.400	4.700	0.173	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.270TYP		0.050TYP		
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ö		1.600		0.063	
$\overline{}$	0.000	0.380	0.000	0.015	